

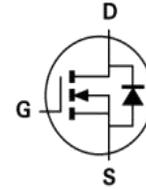


LT15N06AD

N- Channel Advanced Power MOSFET

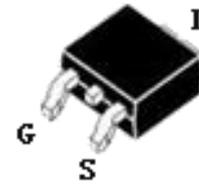
MAIN CHARACTERISTICS

I_D	15A
V_{DSS}	60V
$R_{DS(on)-typ}$ (@ $V_{GS}=10V$)	28m Ω



FEATURES

- Fast Switching
- Low ON Resistance
- Low Gate Charge
- 100% Single Pulse avalanche energy Test



TO-252

APPLICATIONS

- Power switch circuit of adaptor and charger.

MECHANICAL DATA

- Case: Molded plastic
- Mounting Position: Any
- Molded Plastic: UL Flammability Classification Rating 94V-0
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Solder bath temperature 275°C maximum, 10s per JESD 22-B106

Product specification classification

Part Number	Package	Mode Name	Pack
LT15N06AD	TO-252	LT15N06AD	Tape



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Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Continue Drain Current	I_D	15	A
Pulsed Drain Current (Note1)	I_{DM}	50	A
Power Dissipation	P_D	18	W
Single Pulse Avalanche Energy (Note5)	E_{AS}	25	mJ
Operating Temperature Range	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C
Thermal Resistance, Junction to Case(Note 2)	$R_{\theta JC}$	3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62	°C/W

Note1:Pulse test: 300 μs pulse width, 2 % duty cycle

Electrical Characteristics at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_D = 250 \mu A$	BV_{DSS}	60	-	-	V
Drain-Source Leakage Current	$V_{DS} = 60V, V_{GS} = 0 V$	I_{DSS}	-	-	1	μA
	$V_{DS}=60V, T_C=125^\circ C$		-	-	100	μA
Gate Leakage Current	$V_{GS} = \pm 20 V, V_{DS} = 0 V$	I_{GSS}	-	-	±100	nA
Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	$V_{GS(th)}$	1	-	2.5	V
Drain-Source On-State Resistance (Note 3)	$V_{GS} = 10 V, I_D = 10 A$	$R_{DS(on)}$	-	28	37	mΩ
	$V_{GS} = 4.5 V, I_D = 5 A$	$R_{DS(on)}$	-	35	48	mΩ
Forward Transconductance	$V_{DS} = 50 V, I_D = 25 A$	gfs	-	20	-	S
Input Capacitance	$V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz$	C_{iss}	-	1050	-	pF
Output Capacitance		C_{oss}	-	65	-	pF
Reverse Transfer Capacitance		C_{rss}	-	45	-	pF
Turn-on Delay Time		$t_{d(ON)}$	-	2.8	-	ns
Rise Time	VDS=30V, RL=1.5Ω VGS=10V, RG=3Ω (Note3,4)	t_r	-	17	-	ns
Turn-Off Delay Time		$t_{d(OFF)}$	-	20	-	ns
Fall Time		t_f	-	5	-	ns
Total Gate Charge		Q_G	-	19	-	nC
Gate to Source Charge	VDS=30V, ID=10A, VGS=10V (Note3,4)	Q_{GS}	-	2.3	-	nC
Gate to Drain Charge		Q_{GD}	-	4.6	-	nC

Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

Characteristics	Test Condition	Symbol	Min.	Typ.	Max.	Unit
Maximun Body-Diode Continuous Current (Note 2)		I_S	-	-	15	A
Maximun Body-Diode Pulsed Current		I_{SM}	-	-	50	A
Drain-Source Diode Forward Voltage	$I_{SD} = 10A$	V_{SD}	-	-	1.2	V
Reverse Recovery Time	$I_S = I_F, I_{SD}=10A, V_{GS} = 0$	t _{rr}	-	12	-	ns
Reverse Recovery Charge	$V, di/dt = 100 A/\mu s$	Q _{rr}	-	7	-	μC

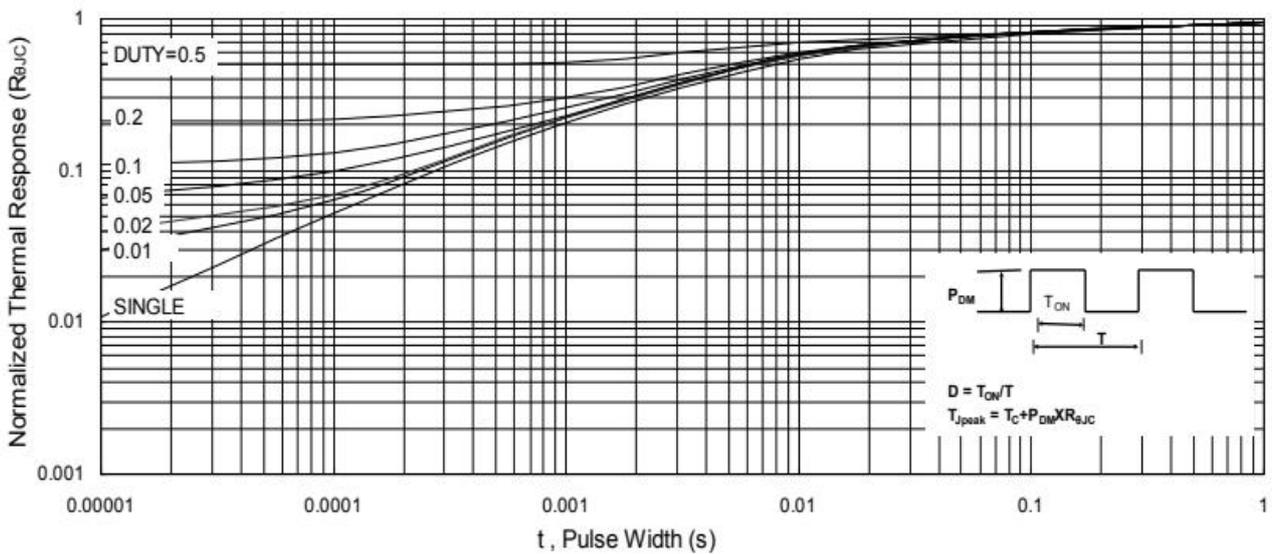
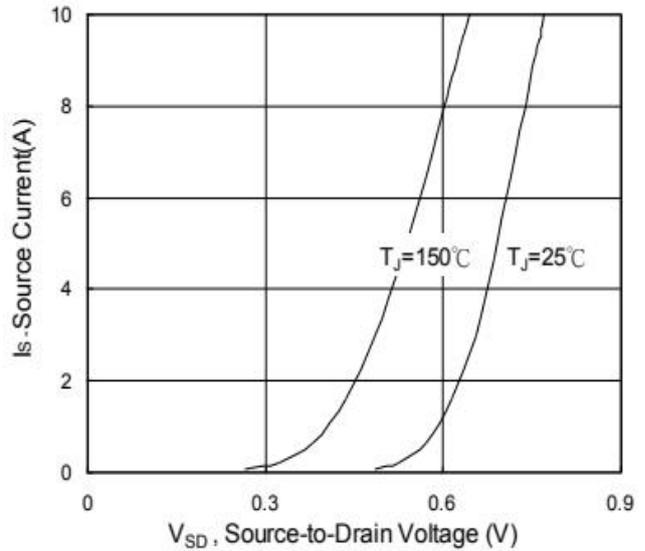
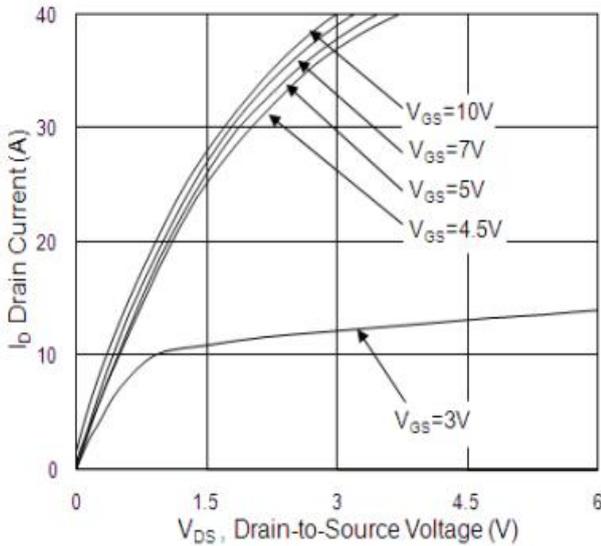
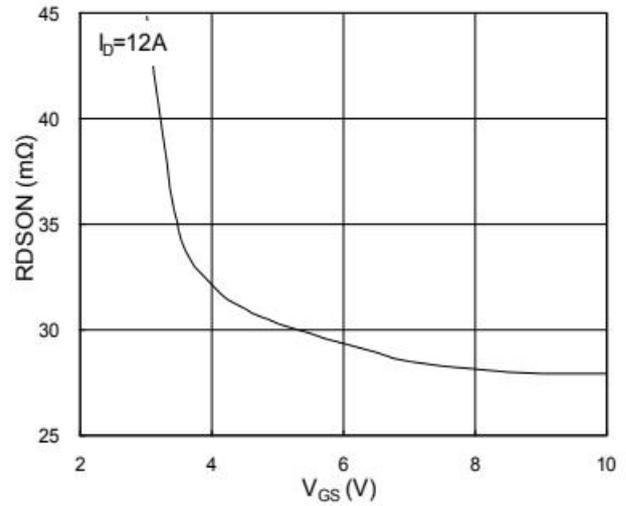
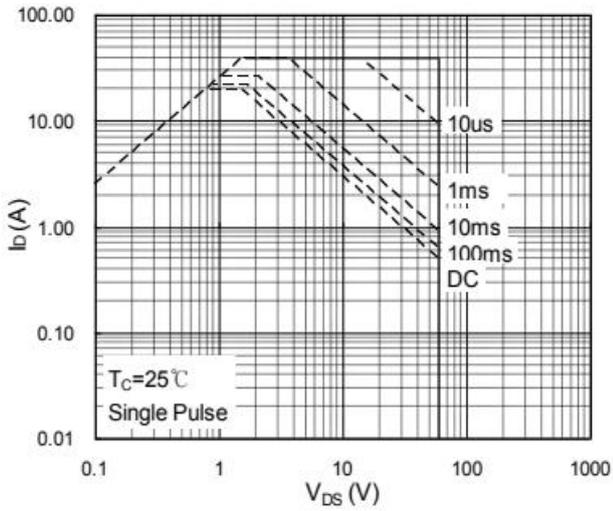
Note2:Pulse test: 300 μs pulse width, 2 % duty cycle



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RATINGS AND CHARACTERISTIC CURVES



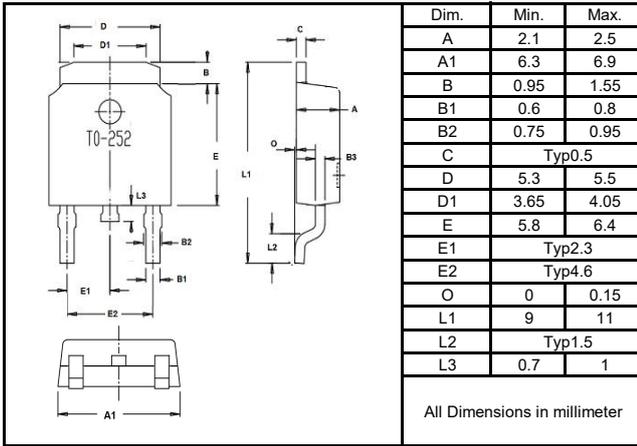


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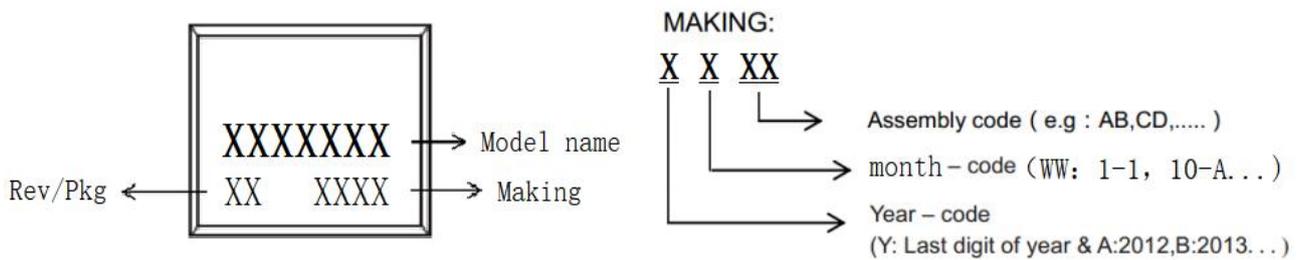
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Package Outline Dimensions millimeters

TO-252



Marking on the body



packing instruction

PKG	最小包装	内盒	外箱
TO-252			
	2500pcs/盘	5000pcs/盒	25000pcs/箱

Notice

All product, product specifications and data are subject to change without notice to improve. The right to explain is owned by LINGXUN electronics

company.

Confirm that operation temperature is within the specified range described in the product specification. Avoid applying power exceeding normal rated

power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.

LINGXUN electronics shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.